L Number	Hits	Search Text	DB	Time stamp
1	2113	438/458.ccls. 438/459.ccls. 438/463.ccls. 438/479.ccls.	USPAT;	2004/07/24 19:46
		438/940.ccls. 438/977.ccls.	US-PGPUB	
3	1140	(gan (gallium adj nitride) (nitride near (compound	USPAT;	2004/07/24 19:54
		semiconductor)) (group near2 nitride)) same laser same	US-PGPUB	
		((growth adj (substrate wafer)) sic (silicon adj carbide)		
_	664	sapphire)	500, 100,	2004/07/24 40:54
5	661	(gan (gallium adj nitride) (nitride near (compound	EPO; JPO;	2004/07/24 19:54
İ		semiconductor)) (group near2 nitride)) and laser and ((growth adj (substrate wafer)) sic (silicon adj carbide)	DERWENT; IBM TDB	
		sapphire)	1011_100	
2	194	(438/458.ccls. 438/459.ccls. 438/463.ccls. 438/479.ccls.	USPAT;	2004/07/24 19:55
-		438/940.ccls. 438/977.ccls.) and (gan (gallium adj nitride)	US-PGPUB	
		(nitride near (compound semiconductor)) (group near2		
		nitride))		
4	174	(gan (gallium adj nitride) (nitride near (compound	USPAT;	2004/07/24 20:13
		semiconductor)) (group near2 nitride)) same (laser with	US-PGPUB	
		(separat\$6 remov\$6 ablat\$6)) same ((growth adj (substrate		
_	40	wafer)) sic (silicon adj carbide) sapphire)	FDO: 100:	2004/07/24 20:12
7	48	(gan (gallium adj nitride) (nitride near (compound	EPO; JPO; DERWENT;	2004/07/24 20:13
		semiconductor)) (group near2 nitride)) and (laser with (separat\$6 remov\$6 ablat\$6)) and ((growth adj (substrate	IBM_TDB	
1		wafer)) sic (silicon adj carbide) sapphire)	101-1-100	
		water // sic (sincorr adj carbide) sapprine)		L